

XPT IGBT

$V_{CES} = 1200V$

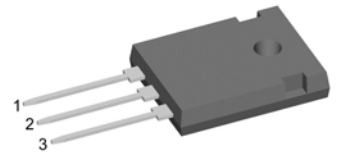
$I_{C25} = 38A$

$V_{CE(sat)} = 1.8V$

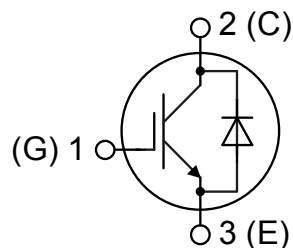
Copack

Part number

IXA20IF1200HB



Backside: collector

**Features / Advantages:**

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μ sec.
 - very low gate charge
 - low EMI
 - square RBSOA @ 3x I_c
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

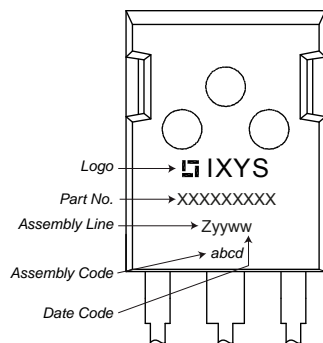
Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

IGBT				Ratings					
Symbol	Definition	Conditions	min.	typ.	max.	Unit			
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}C$			1200	V			
V_{GES}	max. DC gate voltage				± 20	V			
V_{GEM}	max. transient gate emitter voltage				± 30	V			
I_{C25}	collector current	$T_C = 25^{\circ}C$			38	A			
I_{C80}		$T_C = 80^{\circ}C$			22	A			
P_{tot}	total power dissipation	$T_C = 25^{\circ}C$			165	W			
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15A; V_{GE} = 15V$		1.8	2.1	V			
				2.1		V			
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.6mA; V_{CE} = V_{CE}$	5.4	5.9	6.5	V			
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0V$			0.1	mA			
				0.1		mA			
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20V$			500	nA			
$Q_{G(on)}$	total gate charge	$V_{CE} = 600V; V_{GE} = 15V; I_C = 15A$		47		nC			
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600V; I_C = 15A$ $V_{GE} = \pm 15V; R_G = 56\Omega$							
t_r	current rise time						$T_{VJ} = 125^{\circ}C$	70	ns
$t_{d(off)}$	turn-off delay time						40	ns	
t_f	current fall time						250	ns	
E_{on}	turn-on energy per pulse						100	ns	
E_{off}	turn-off energy per pulse						1.55	mJ	
E_{off}		1.7	mJ						
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15V; R_G = 56\Omega$							
I_{CM}		$V_{CEmax} = 1200V$			45	A			
SCSOA	short circuit safe operating area	$V_{CEmax} = 900V$							
t_{sc}	short circuit duration	$V_{CE} = 900V; V_{GE} = \pm 15V$			10	μs			
I_{sc}	short circuit current	$R_G = 56\Omega; \text{non-repetitive}$			60	A			
R_{thJC}	thermal resistance junction to case				0.76	K/W			
R_{thCH}	thermal resistance case to heatsink				0.25	K/W			
Diode									
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}C$			1200	V			
I_{F25}	forward current	$T_C = 25^{\circ}C$			45	A			
I_{F80}		$T_C = 80^{\circ}C$			24	A			
V_F	forward voltage	$I_F = 20A$			2.20	V			
					1.95	V			
I_R	reverse current	$V_R = V_{RRM}$			*	mA			
	* not applicable, see Ices value above				*	mA			
Q_{rr}	reverse recovery charge	$V_R = 600V$ $-di_F/dt = -400A/\mu s$ $I_F = 20A; V_{GE} = 0V$							
I_{RM}	max. reverse recovery current						$T_{VJ} = 125^{\circ}C$	3	μC
t_{rr}	reverse recovery time						20	A	
E_{rec}	reverse recovery energy						350	ns	
R_{thJC}	thermal resistance junction to case				0.9	K/W			
R_{thCH}	thermal resistance case to heatsink				0.25	K/W			

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part number

I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 20 = Current Rating [A]
 IF = Copack
 1200 = Reverse Voltage [V]
 HB = TO-247AD (3)

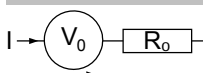
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA20IF1200HB	IXA20IF1200HB	Tube	30	508460

Similar Part	Package	Voltage class
IXA20I1200PB	TO-220AB (3)	1200

Equivalent Circuits for Simulation

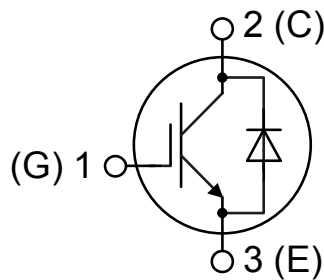
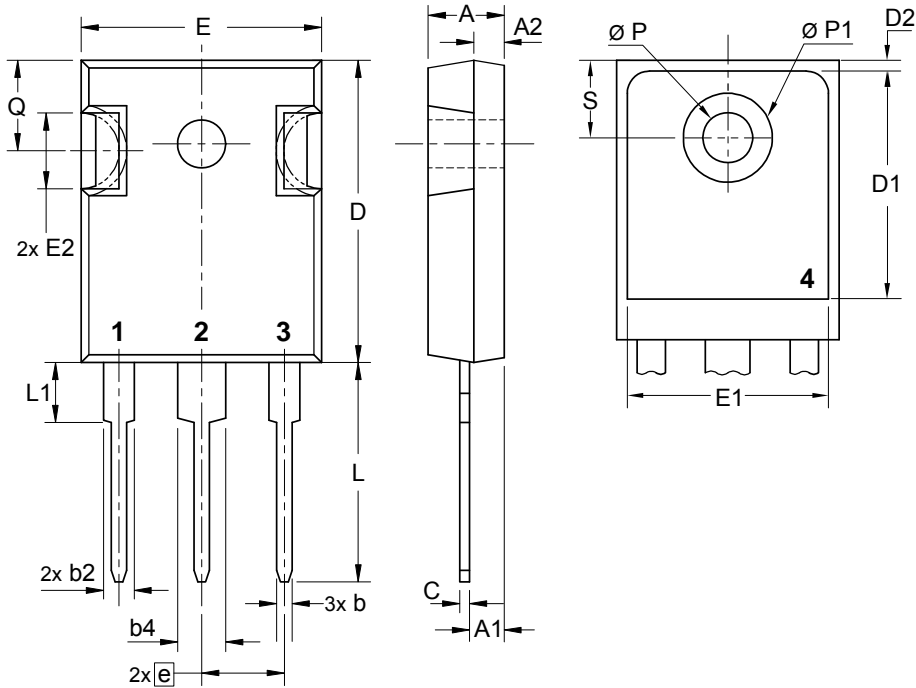
* on die level

$T_{VJ} = 150\text{ }^{\circ}\text{C}$



	IGBT	Diode	
$V_{0\ max}$ threshold voltage	1.1	1.25	V
$R_{0\ max}$ slope resistance *	86	42.5	mΩ

Outlines TO-247



IGBT

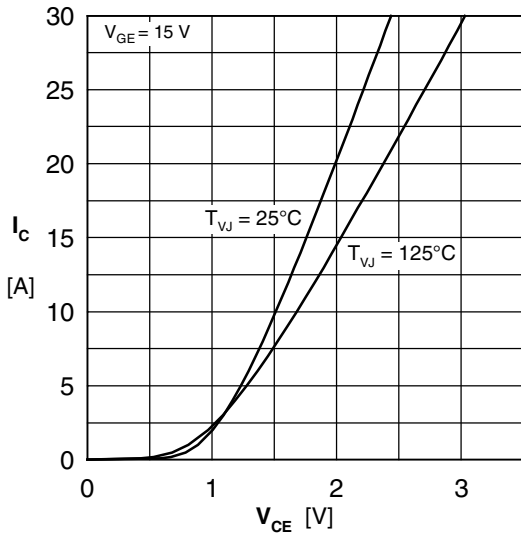


Fig. 1 Typ. output characteristics

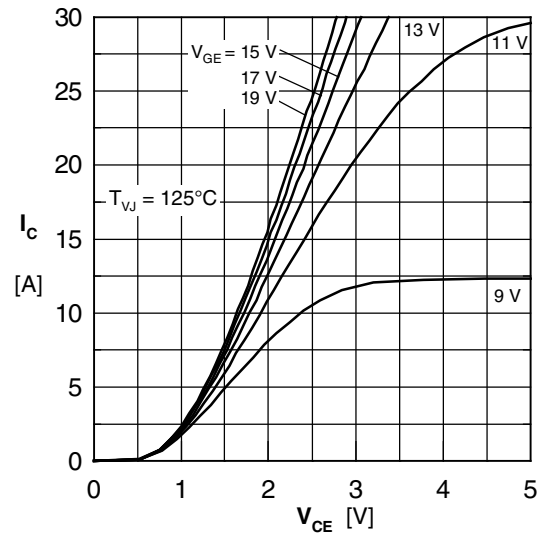


Fig. 2 Typ. output characteristics

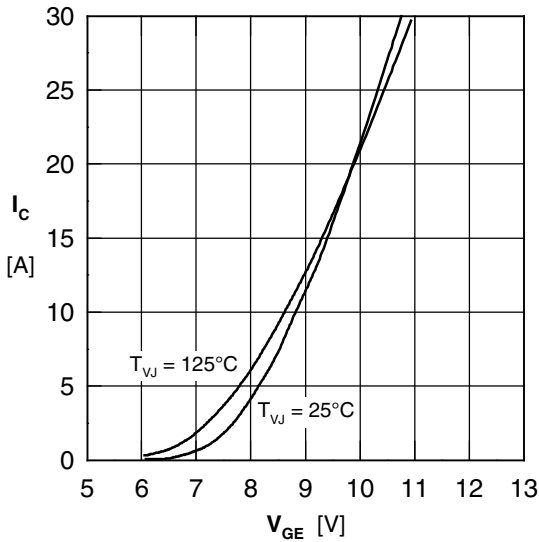


Fig. 3 Typ. transfer characteristics

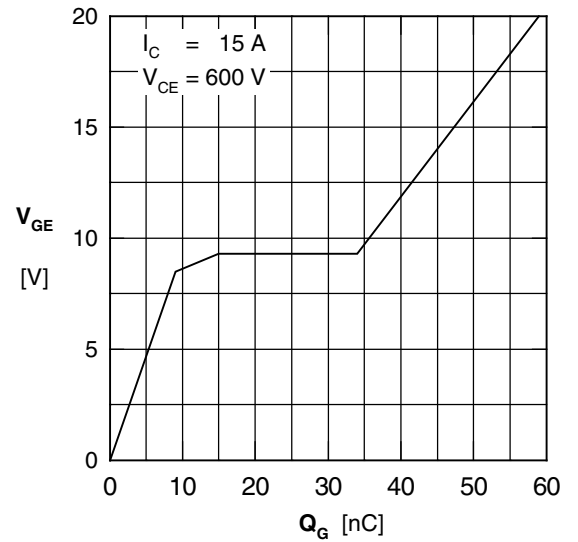


Fig. 4 Typ. turn-on gate charge

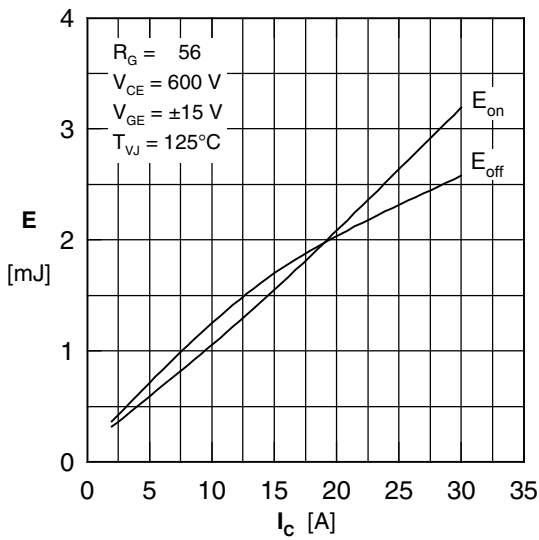


Fig. 5 Typ. switching energy vs. collector current

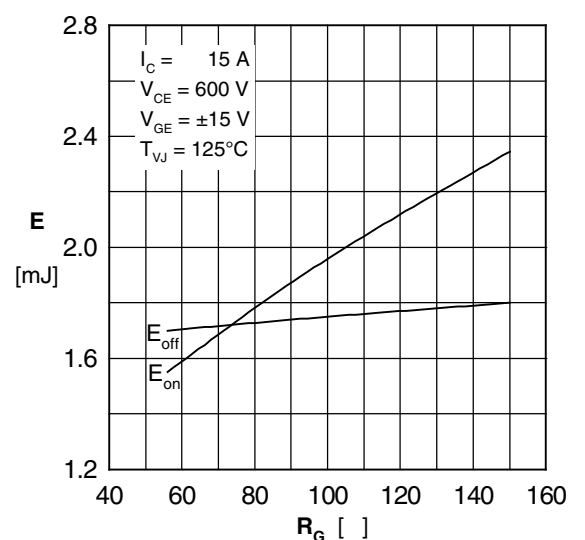


Fig. 6 Typ. switching energy vs. gate resistance

Diode

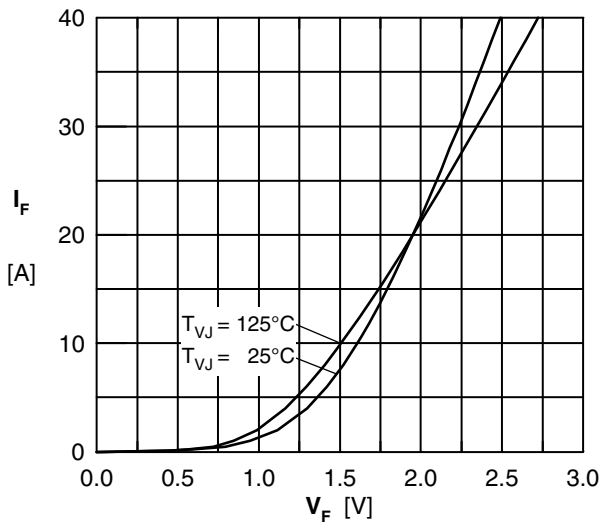


Fig. 7 Typ. Forward current versus V_F

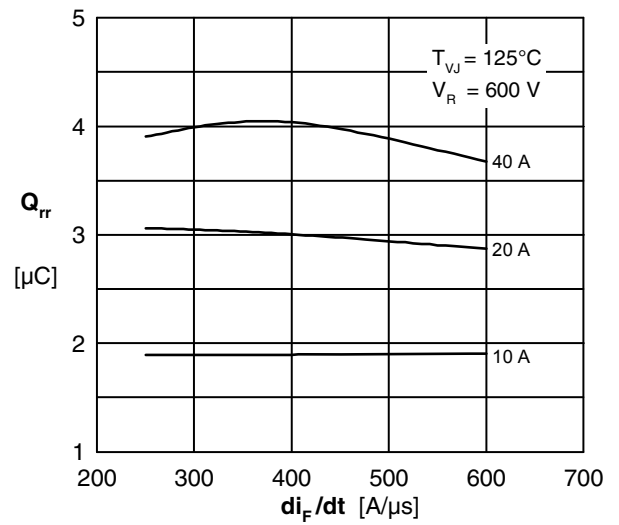


Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

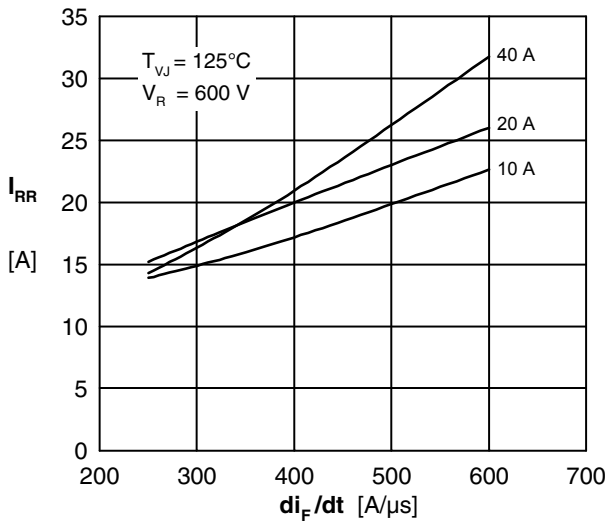


Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

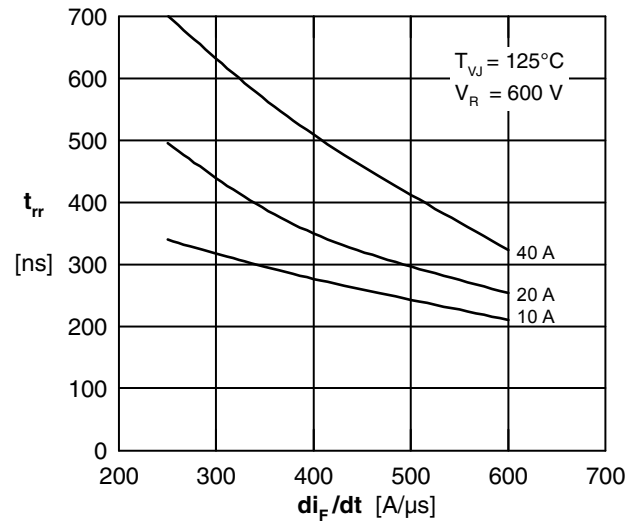


Fig. 10 Typ. recovery time t_{rr} versus di/dt

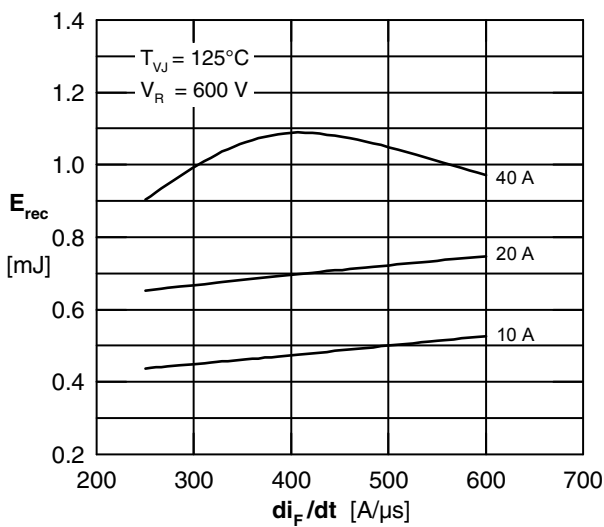


Fig. 11 Typ. recovery energy E_{rec} versus di/dt

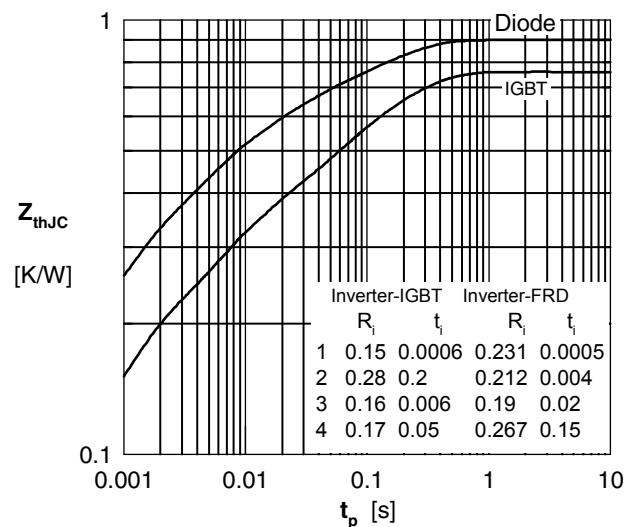


Fig. 12 Typ. transient thermal impedance